

IGBT

GD300HFL120C2S

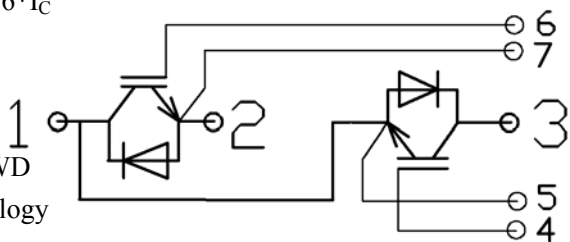
Molding Type Module

1200V/300A 2 in one-package



Features

- High short circuit capability, self limiting to $6 \cdot I_C$
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Equivalent Circuit Schematic

Typical Applications

- AC inverter drives
- Switching mode power supplies
- Electronic welders

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Description	GD300HFL120C2S	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V

Symbol	Description	GD300HFL120C2S	Units
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$, $T_J=150^{\circ}\text{C}$ @ $T_C=80^{\circ}\text{C}$, $T_J=150^{\circ}\text{C}$	620	A
		300	
$I_{CM(1)}$	Pulsed Collector Current $t_p=1\text{ms}$	600	A
I_F	Diode Continuous Forward Current	300	A
I_{FM}	Diode Maximum Forward Current	600	A
P_D	Maximum power Dissipation @ $T_J=150^{\circ}\text{C}$	2500	W
T_{SC}	Short Circuit Withstand Time @ $T_J=125^{\circ}\text{C}$	10	μs
T_J	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
I^2t -value, Diode	$V_R=0\text{V}$, $t=10\text{ms}$, $T_J=125^{\circ}\text{C}$	19000	A^2s
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V
Mounting Torque	Power Terminal Screw:M6	2.5 to 5	N.m
	Mounting Screw:M6	3 to 6	N.m

Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

Electrical Characteristics of IGBT $T_C=25^{\circ}\text{C}$ unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$T_J=25^{\circ}\text{C}$	1200			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}$, $V_{GE}=0\text{V}$, $T_J=25^{\circ}\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}$, $V_{CE}=0\text{V}$, $T_J=25^{\circ}\text{C}$			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=12\text{mA}$, $V_{CE}=V_{GE}$, $T_J=25^{\circ}\text{C}$	5	6.2	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=300\text{A}$, $V_{GE}=15\text{V}$, $T_J=25^{\circ}\text{C}$		1.9		V
		$I_C=300\text{A}$, $V_{GE}=15\text{V}$, $T_J=125^{\circ}\text{C}$		2.1		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}$, $I_C=300\text{A}$, $R_G=4.7\Omega$, $V_{GE}=\pm 15\text{V}$, $T_J=25^{\circ}\text{C}$		90		ns
t_r	Rise Time			55		ns
$t_{d(off)}$	Turn-Off Delay Time			460		ns
t_f	Fall Time			55		ns

GD300HFL120C2S**IGBT Module**

E_{on}	Turn-On Switching Loss	$V_{CC}=600V, I_C=300A,$ $R_G=4.7\Omega, V_{GE}=\pm 15V,$ $T_J=25^\circ C$		28		mJ
E_{off}	Turn-Off Switching Loss			25		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=300A,$ $R_G=4.7\Omega, V_{GE}=\pm 15V,$ $T_J=125^\circ C$		110		ns
t_r	Rise Time			60		ns
$t_{d(off)}$	Turn-Off Delay Time			500		ns
t_f	Fall Time			60		ns
E_{on}	Turn-On Switching Loss			31		mJ
E_{off}	Turn-Off Switching Loss			27		mJ
C_{ies}	Input Capacitance	$V_{CE}=25V, f=1MHz,$ $V_{GE}=0V$		21		nF
C_{oes}	Output Capacitance			1.5		nF
C_{res}	Reverse Transfer Capacitance			0.9		nF
I_{SC}	SC Data	$t_{SC}\leq 10\mu s, V_{GE}=15V,$ $T_J=125^\circ C, V_{CC}=900V,$ $V_{CEM}\leq 1200V$		1300		A
R_{Gint}	Internal gate resistance			2		Ω
L_{CE}	Stray inductance				20	nH
$R_{CC'+EE'}$	Module lead resistance, terminal to chip	$T_C=25^\circ C$		0.35		m Ω

Electrical Characteristics of DIODE $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _F	Diode Forward Voltage	I _F =300A	T _J =25℃		2.0		V
			T _J =125℃		2.2		
Q _r	Diode Reverse Recovery Charge	I _F =300A, V _R =600V, di/dt=-2400A/μs, V _{GE} =-15V	T _J =25℃		27		μC
			T _J =125℃		50		
I _{RM}	Diode Peak Reverse Recovery Current		T _J =25℃		120		A
			T _J =125℃		170		
E _{rec}	Reverse Recovery Energy		T _J =25℃		9		mJ
			T _J =125℃		20		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)		0.05	K/W
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)		0.12	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.035		K/W
Weight	Weight of Module	300		g

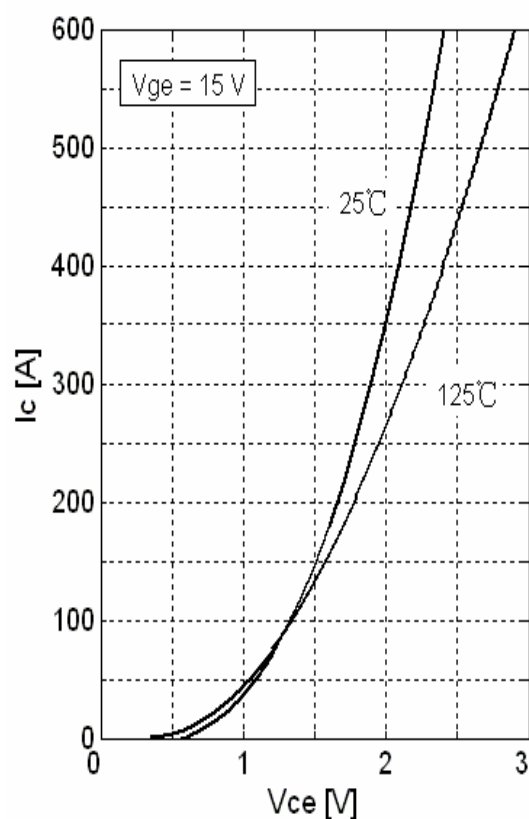


Fig 1. Typical Output Characteristics

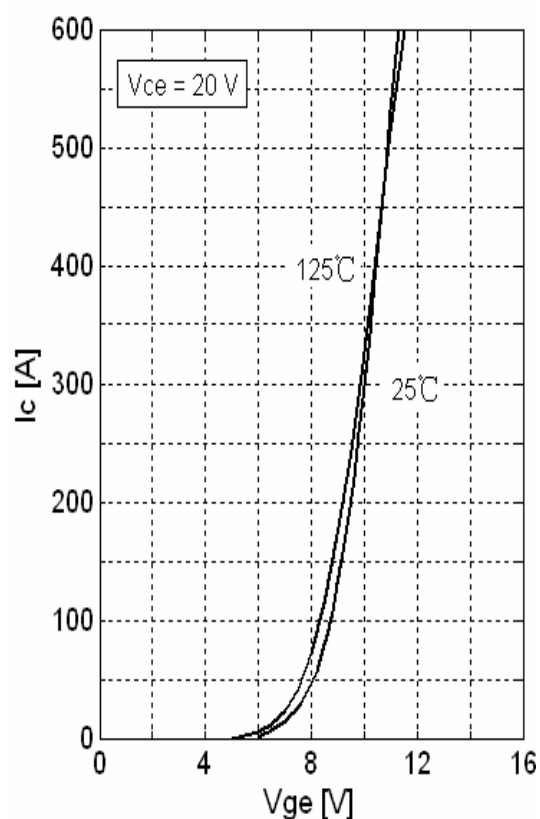


Fig 2. Typical Transfer Characteristics

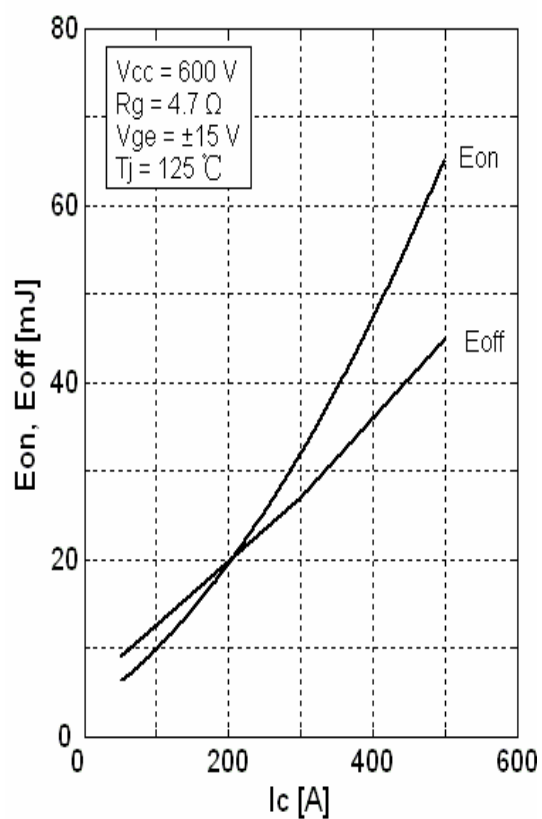


Fig 3. Switching Loss vs Collector Current

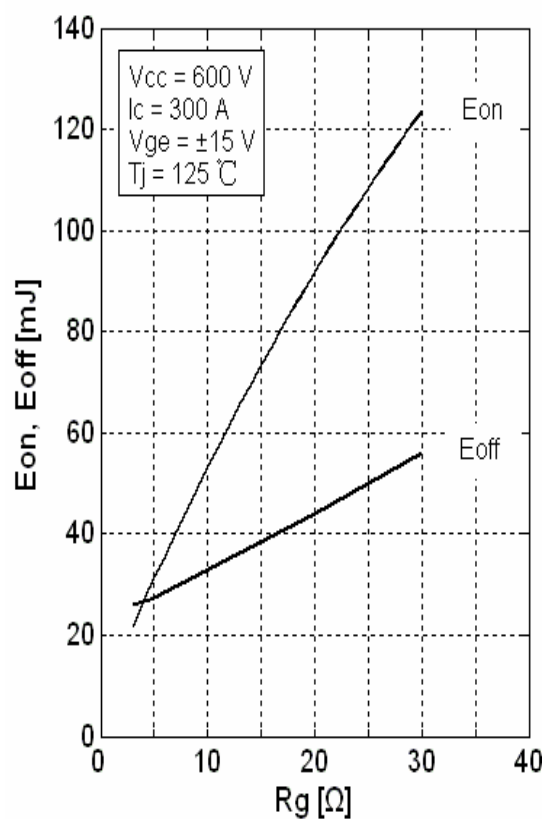


Fig 4. Switching Loss vs Gate Resistor

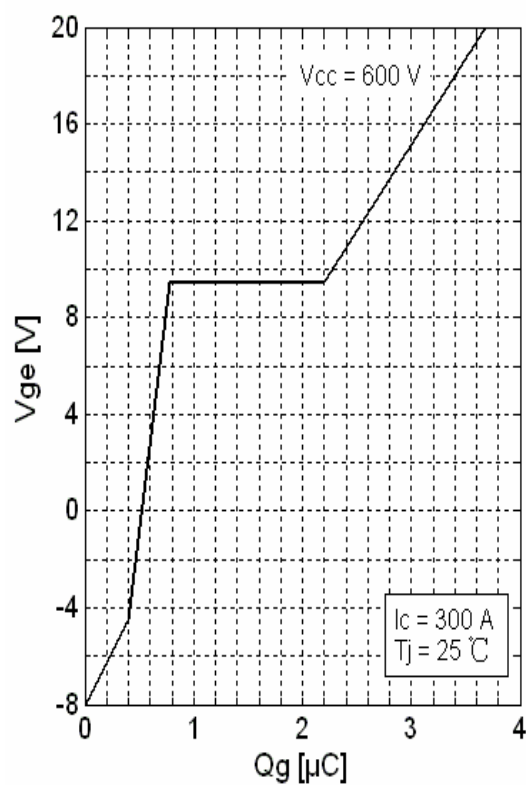
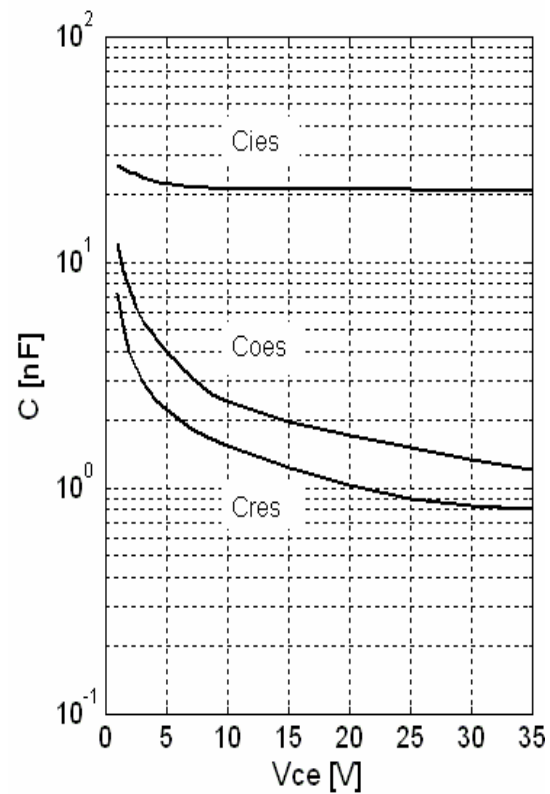
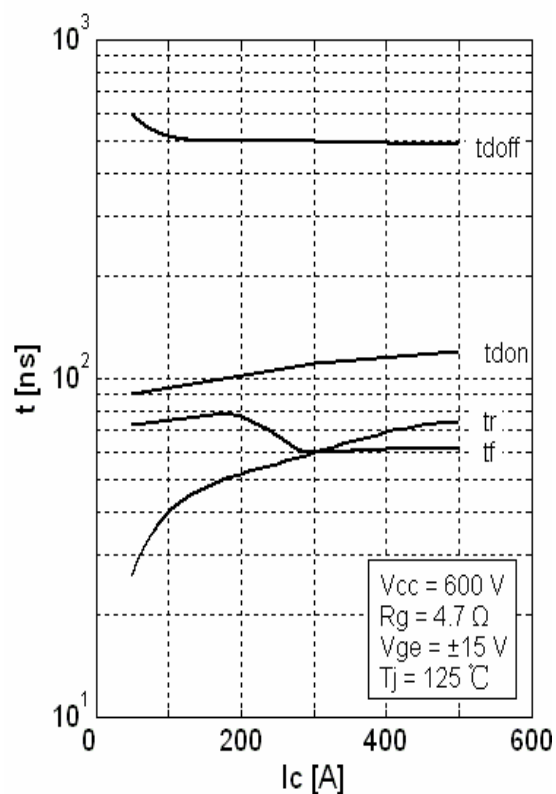
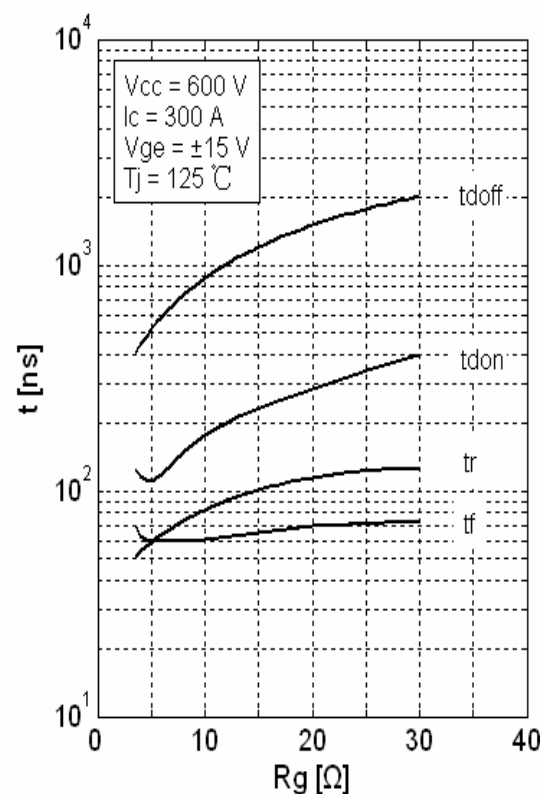


Fig 5. Gate Charge Characteristics.

Fig 6. Typical Capacitance vs
Collector-Emitter VoltageFig 7. Typical Switching Times vs I_c Fig 8. Typical Switching Times vs
Gate Resistance R_g

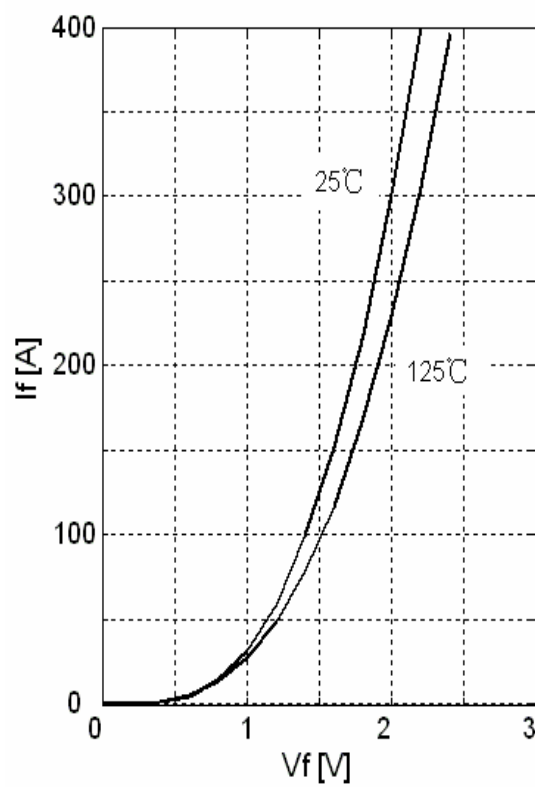


Fig 9. Typical Forward Characteristics (diode)

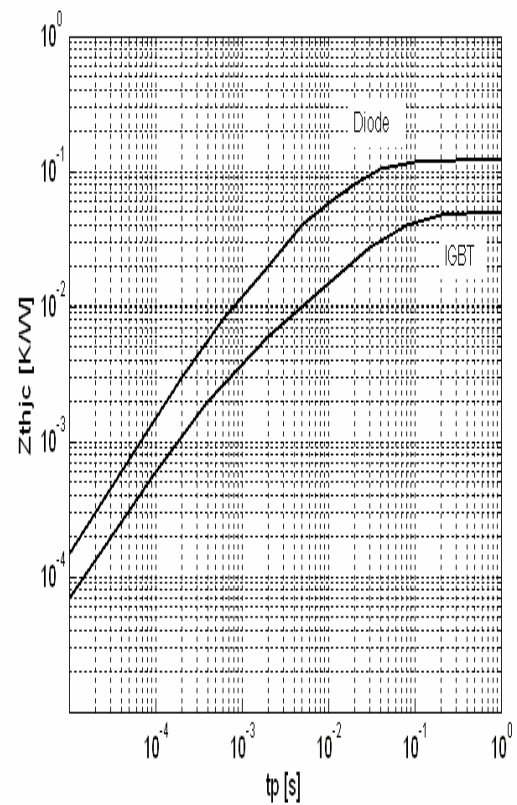


Fig 10. Transient thermal impedance

Dimensions in Millimeters

